

CentralTM Semiconductor Corp.

145 Adams Avenue, Hauppauge, NY 11788 USA
Tel: (631) 435-1110 • Fax: (631) 435-1824

Manufacturers of World Class Discrete Semiconductors

CEN-U45

NPN SILICON
DARLINGTON TRANSISTOR

JEDEC TO-202 CASE

DESCRIPTION

The CENTRAL SEMICONDUCTOR CEN-U45 type is a NPN Silicon Monolithic Darlington Transistor designed for applications requiring high gain and high power dissipation.

MAXIMUM RATINGS ($T_A=25^\circ\text{C}$)

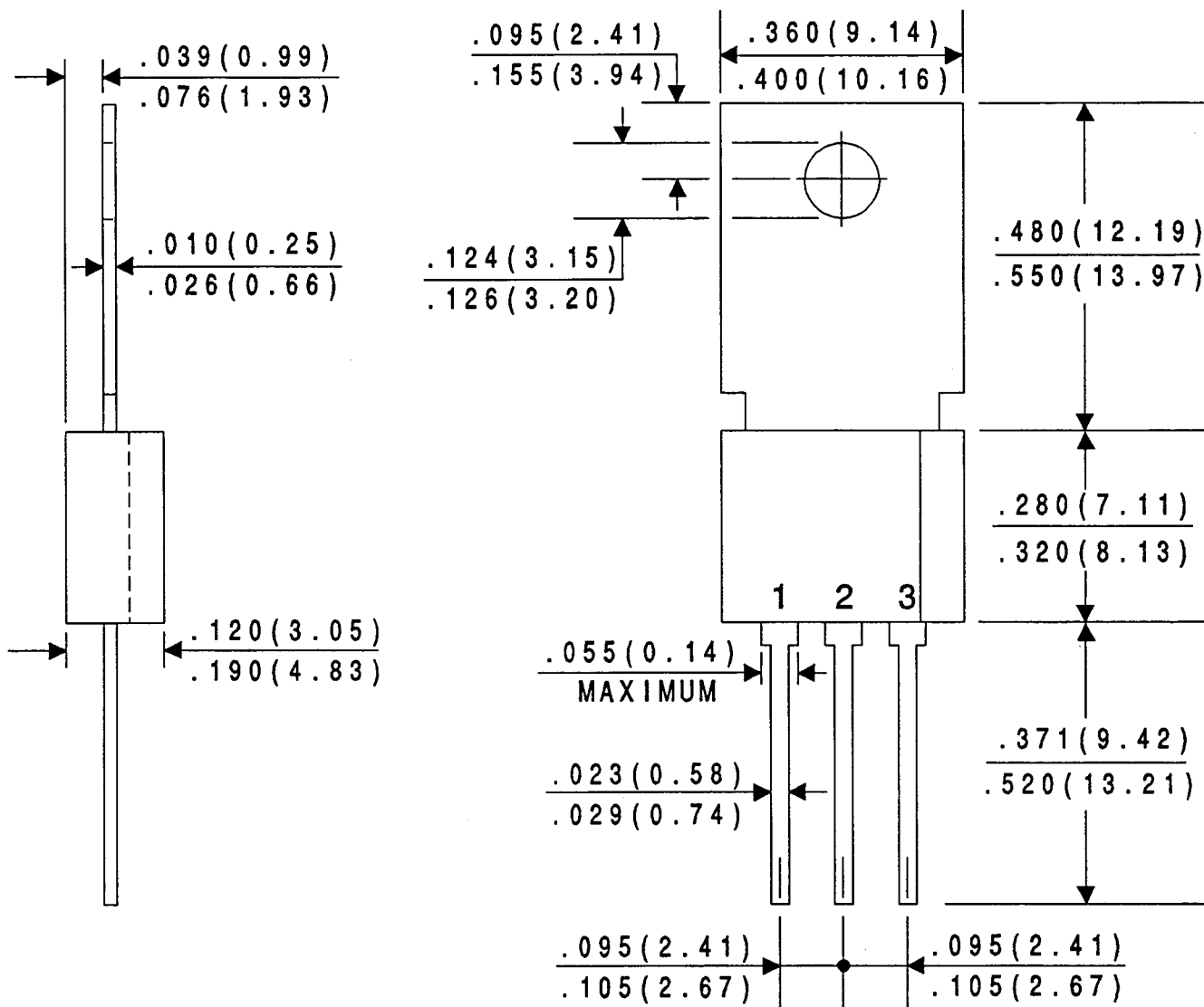
	<u>SYMBOL</u>		<u>UNITS</u>
Collector-Base Voltage	V_{CBO}	50	V
Collector-Emitter Voltage	V_{CES}	40	V
Collector-Emitter Voltage	V_{CEO}	40	V
Emitter-Base Voltage	V_{EBO}	12	V
Collector Current	I_C	2.0	A
Power Dissipation	P_D	2.0	W
Power Dissipation ($T_C=25^\circ\text{C}$)	P_D	10	W
Operating and Storage			
Junction Temperature	T_J, T_{stg}	-65 to +150	$^\circ\text{C}$
Thermal Resistance	θ_{JA}	62.5	$^\circ\text{C/W}$
Thermal Resistance	θ_{JC}	12.5	$^\circ\text{C/W}$

ELECTRICAL CHARACTERISTICS ($T_A=25^\circ\text{C}$ unless otherwise noted)

<u>SYMBOL</u>	<u>TEST CONDITIONS</u>	<u>MIN</u>	<u>MAX</u>	<u>UNITS</u>
I_{CBO}	$V_{CB}=30\text{V}$		100	nA
I_{EBO}	$V_{EB}=10\text{V}$		100	nA
BV_{CBO}	$I_C=100\mu\text{A}$	50		V
BV_{CES}	$I_C=100\mu\text{A}$	40		V
BV_{EBO}	$I_E=10\mu\text{A}$	12		V
$V_{CE(SAT)}$	$I_C=1.0\text{A}, I_B=200\text{mA}$		1.0	V
$V_{BE(SAT)}$	$I_C=1.0\text{A}, I_B=200\text{mA}$		2.0	V
$V_{BE(ON)}$	$V_{CE}=5.0\text{V}, I_C=1.0\text{A}$		2.0	V
h_{FE}	$V_{CE}=5.0\text{V}, I_C=200\text{mA}$	25K	150K	
h_{FE}	$V_{CE}=5.0\text{V}, I_C=500\text{mA}$	15K		
h_{FE}	$V_{CE}=5.0\text{V}, I_C=1.0\text{A}$	4.0K		
f_T	$V_{CE}=5.0\text{V}, I_C=200\text{mA}, f=100\text{MHz}$	100		MHz
C_{ob}	$V_{CB}=10\text{V}, I_E=0, f=1.0\text{MHz}$		8.0	pF

(SEE REVERSE SIDE)

JEDEC TO-202 CASE - MECHANICAL OUTLINE



All Dimensions in Inches (mm).

LEAD CODE:

- 1) EMITTER
- 2) BASE
- 3) COLLECTOR